TOSHIBA Transistor Silicon NPN Epitaxial Type

TPCP8701

Portable Equipment Applications
Switching Applications
Inverter Lighting Applications

- · Small footprint due to small and thin package
- High DC current gain : $h_{FE} = 400 \text{ to } 1000 \text{ (IC} = 0.3 \text{ A)}$
- Low collector-emitter saturation : VCE(sat) = 0.14 V(max)
- High-speed switching : $t_f = 120 \text{ ns (typ.)}$

Maximum Ratings (Ta = 25°C)

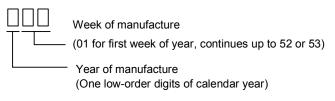
Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	100	V	
Collector-emitter voltage		V _{CEX}	80	V	
		V _{CEO}	50	V	
Emitter-base voltage		V_{EBO}	7	٧	
Collector current	DC (Note 1)	IC	3.0	А	
	Pulse (Note 1)	I _{CP}	5.0		
Base current		Ι _Β	300	mA	
Collector power dissipation (t = 10s)	Single-device operation		1.77	W	
	Single-device value at dual operation	Pc (Note 2)	0.95		
Collector power dissipation (DC)	Single-device operation		0.94		
	Single-device value at dual operation	Pc (Note 2)	0.54	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

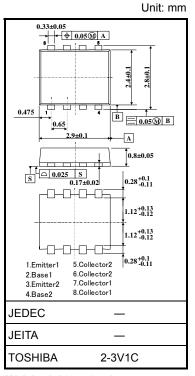
Note 1: Please use devices on condition that the junction temperature is below 150°C.

Note 2: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

Note 3: ● on lower left on the marking indicates Pin 1.

Weekly code: (Three digits)





Weight: 0.017 g (typ.)

Figure 1.
Circuit configuration
(Top View)

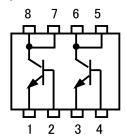
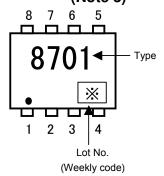


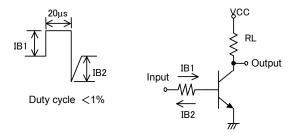
Figure 2. Marking (Note 3)



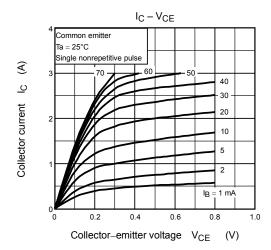
Electrical Characteristics (Ta = 25°C)

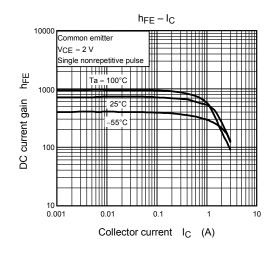
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	V _{CB} = 100 V, I _E = 0	_	_	100	nA
Emitter cut-off current		I _{EBO}	$V_{EB} = 7 \text{ V, } I_{C} = 0$	_	_	100	nA
Collector-emitter brakedown voltage		V _{(BR) CEO}	$I_C = 10 \text{ mA}, I_B = 0$	50	_	_	٧
DC current gain		h _{FE} (1)	$V_{CE} = 2 \text{ V}, I_{C} = 0.3 \text{ A}$	400	_	1000	
		h _{FE} (2)	V _{CE} = 2 V, I _C = 1 A	200	_	_	
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 1 A, I _B = 20 mA	_	_	0.14	V
Base-emitter saturation voltage		V _{BE (sat)}	$I_C = 1 \text{ A}, I_B = 20 \text{ mA}$	_	_	1.10	٧
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1MHz	_	13	_	pF
Switching time	Rise time	t _r	See Figure 3 circuit diagram $V_{CC} \simeq 30 \text{ V, R}_L = 30 \Omega$	_	40	_	ns
	Storage time	t _{stg}		_	500	_	
	Fall time	t _f	$I_{B1} = -I_{B2} = 33.3 \text{ mA}$	_	120	_	

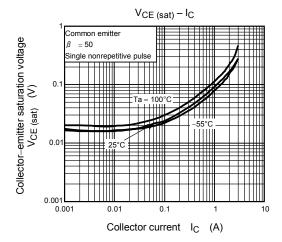
Figure 3. Switching Time Test Circuit & Timing Chart

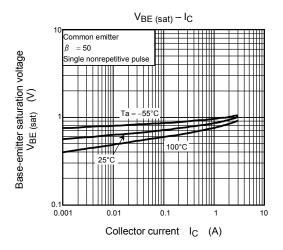


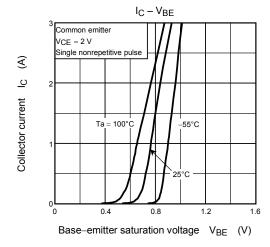
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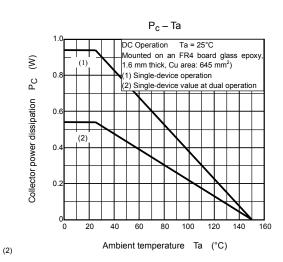




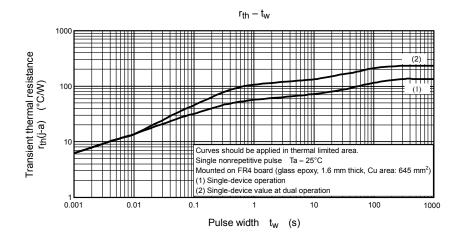


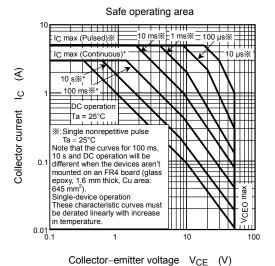


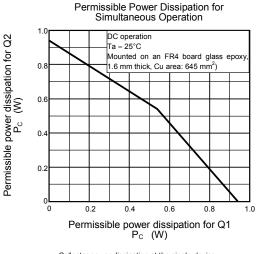




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Collector power dissipation at the single-device operation is 0.94W. $\label{eq:collector} % \begin{subarray}{ll} \end{subarray} % \begin{subarr$

Collector power dissipation at the single-device value at dual operation is 0.54W. $\label{eq:collector} % \begin{subarray}{ll} $ & & & & \\ \hline \end{subarray}$

Collector power dissipation at the dual operation is set to 1.08W.

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Handbook" etc..

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